



PNP Small Signal Silicon Transistor

Qualified per MIL-PRF-19500/511

Qualified Levels: JAN, JANTX, JANTXV and JANS

DESCRIPTION

This 2N4261 small signal transistor comes in a hermetically sealed metal TO-72 package and is military qualified for high-reliability applications. It is also available in a low-profile UB surface mount package or with a ceramic lid in the UBC package.

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FEATURES

- Popular JEDEC registered 2N4261 number
- JAN, JANTX, JANTXV and JANS qualification is available per MIL-PRF-19500/511.
 (See <u>part nomenclature</u> for all available options.)
- · RoHS compliant version available

APPLICATIONS / BENEFITS

- Leaded, hermetically sealed TO-72 package
- Lightweight
- · Military and other high-reliability applications

TO-72 Package

Also available in:

UB package (surface mount)
2N4261UB

UBC package (Ceramic Lid surface mount)

2N4261UBC

MAXIMUM RATINGS @ T_A = 25 °C

Parameters/Test Conditions	Symbol	Value	Unit	
Junction and Storage Temperature	T _J & T _{STG}	-65 to +200	°C	
Thermal Resistance Junction-to-An	nbient ⁽¹⁾	R _{OJA}	0.860	°C/W
Collector – Emitter Voltage		V_{CEO}	-15	V
Collector – Base Voltage		V _{CBO}	-15	V
Emitter - Base Voltage		V_{EBO}	-4.5	V
Total Power Dissipation (1)	@ $T_A = +25 {}^{\circ}C^{(1)}$ @ $T_C = +25 {}^{\circ}C^{(2)}$	P _T	0.2	W
Collector Current		Ic	-30	mA

NOTES: 1. Derate linearly 1.14 mW/°C above T_A = +25°C

MSC - Lawrence

6 Lake Street, Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

MSC - Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

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MECHANICAL and PACKAGING

- CASE: Ni plated kovar, Ni cap
- TERMINALS: Gold over nickel plated kovar leads, solder dipped. RoHS compliant are available without solder dip on commercial grade only.
- MARKING: Manufacturer's ID, date code, part number
- POLARITY: PNP, see case outline on last page
- WEIGHT: Approximately 0.322 grams
- See Package Dimensions on last page.

PART NOMENCLATURE JAN 2N4261 Reliability Level JAN = JAN level JANTX = JANTX level JANTXV = JANTXV level JANS = JANS level Blank = Commercial grade

	SYMBOLS & DEFINITIONS				
Symbol	Definition				
I _B	Base current: The value of the dc current into the base terminal.				
Ic	Collector current: The value of the dc current into the collector terminal.				
V_{CB}	Collector-base voltage: The dc voltage between the collector and the base.				
V _{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.				
V _{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.				
V _{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.				
V _{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.				
V _{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.				
V _{EB}	Emitter-base voltage: The dc voltage between the emitter and the base				



ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

Parameters / Test Conditions	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage I _C = -10 mA	$V_{(BR)CEO}$	-15		V		
Collector-Base Cutoff Current V _{CB} = -15 V	I _{CBO}		-10	μΑ		
Emitter-Base Cutoff Current V _{EB} = -4.5 V	I _{EBO}		-10	μΑ		
Collector-Emitter Cutoff Current $V_{CE} = -10 \text{ V}, V_{BE} = -0.4 \text{ V}$ $V_{CE} = -10 \text{ V}, V_{BE} = -2.0 \text{ V}$	I _{CEX}		-50 -5	nA nA		
ON CHARACTERISTICS (1)						
Forward-Current Transfer Ratio $I_C = -1.0 \text{ mA}, V_{CE} = -1.0 \text{ V}$ $I_C = -10 \text{ mA}, V_{CE} = -1.0 \text{ V}$ $I_C = -30 \text{ mA}, V_{CE} = -1.0 \text{ V}$	h _{FE}	25 30 20	150			
Collector-Emitter Saturation Voltage $I_C = -1.0 \text{ mA}, I_B = -0.1 \text{ mA}$ $I_C = -10 \text{ mA}, I_B = -1.0 \text{ mA}$	V _{CE(sat)}		-0.15 -0.35	V		
Base-Emitter Saturation Voltage (Non-Saturated) V_{CE} = -1.0 V, I_{C} = -1.0 mA V_{CE} = -1.0 V, I_{C} = -10 mA	V _{BE}		-0.8 -1.0	V		

DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min	Max	Unit
Magnitude of Small-Signal Forward Current Transfer				
Ratio	h _{fe}			
$I_C = -5.0 \text{ mA}, V_{CE} = -4.0 \text{ V}, f = 100 \text{ MHz}$	fe	15		
$I_C = -10 \text{ mA}, V_{CE} = -10 \text{ V}, f = 100 \text{ MHz}$		20		
Output Capacitance	0		2.5	pF
$V_{CB} = -4 \text{ V}, I_{E} = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	C _{obo}			
Input Capacitance	C _{ibo}		2.5	pF
$V_{EB} = -0.5V, I_C = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz}$	Oibo		2.0	PΓ

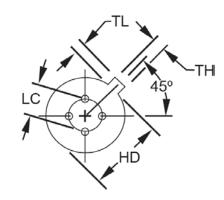
SWITCHING CHARACTERISTICS

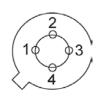
Parameters / Test Conditions	Symbol	Min	Max	Unit
Turn-On Time $V_{CC} = -17 \text{ V}; I_C = -10 \text{ mA}$	ton		2.5	ns
Turn-Off Time $V_{CC} = -17 \text{ V}; I_C = -10 \text{ mA}$	t _{off}		3.5	ns

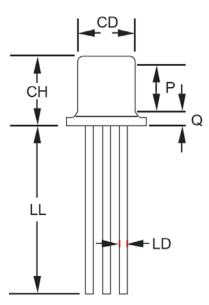
(1) Pulse Test: pulse width = 300 μ s, duty cycle \leq 2.0%



PACKAGE DIMENSIONS







	Dimensions				
Ltr	Inch		Millimeters		Notes
	Min	Max	Min	Max	
TL	0.028	0.048	0.071	1.22	
TH	0.036	0.046	0.091	1.17	
HD	0.209	0.230	5.31	5.84	5
CD	0.178	0.195	4.52	4.95	5
LD	0.016	0.021	0.410	0.53	7, 8
LC	0.100	0.100 TP		I TP	7, 8
CH	0.170	0.210	4.32	5.33	
LL	0.500	0.750	12.70	19.05	7, 8
Р	0.100		2.54		
Q		0.040		1.02	5
1	Emitter				
2	Base				
3	Collector				
4	Case				

NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for information only.
- 3. Beyond r (radius) maximum, TH shall be held for a minimum length of 0.011 (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- 5. Body contour optional within zone defined by HD, CD, and Q.
- 6. Leads at gauge plane 0.054 +0.001 -0.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within 0.007 inch (0.18mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
- 7. Dimension LU applies between L1 and L2. Dimension LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 8. All four leads.
- 9. Dimension r (radius) applies to both inside corners of tab.
- 10. In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- 11. Lead 1 = emitter, lead 2 = base, lead 3 = collector, lead 4 = case (electrically connected).

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